

Vishay Siliconix

# Automotive P-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	-40		
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.094		
$R_{DS(on)}\left(\Omega\right)$ at $V_{GS}$ = -4.5 V	0.188		
I <sub>D</sub> (A)	-4.1		
Configuration	Single		

#### **FEATURES**

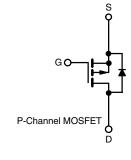
- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE





Marking Code: 9Axxx

ORDERING INFORMATION				
Package	SOT-23			
Lead (Pb)-free and Halogen-free	SQ2389ES-T1-GE3			

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		$V_{DS}$	-40	V
Gate-Source Voltage		$V_{GS}$	± 20	
Continuous Drain Current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	-4.1	
	T <sub>C</sub> = 125 °C		-2.4	
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	-3.6	Α
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	-16	
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	-12	
Single Pulse Avalanche Energy	L=0.11III	E <sub>AS</sub>	7.2	mJ
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	D	3	W
	T <sub>C</sub> = 125 °C	$P_D$	1	VV
Operating Junction and Storage Temperature I	Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount b	$R_{thJA}$	166	°C/W	
Junction-to-Foot (Drain)		$R_{thJF}$	50	C/VV	

#### Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. When mounted on 1" square PCB (FR4 material).



## Vishay Siliconix

PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static		-				l	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-40	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = -250 \mu A$		-2.0	-2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V	-	-	-1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 125 °C	1	-	-50	μΑ
		$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 175 °C	=	-	-150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	V <sub>DS</sub> ≤ -5 V	-10	-	-	Α
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -3 A	1	0.084	0.094	
Drain-Source On-State Resistance a	B	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -3 A, T <sub>J</sub> = 125 °C	-	-	0.144	Ω
Drain-Source On-State nesistance "	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -3 A, T <sub>J</sub> = 175 °C	-	-	0.169	
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -3 A	=	0.140	0.188	
Forward Transconductance b	9fs	V <sub>DS</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -3 A		5	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>		V <sub>DS</sub> = -20 V, f = 1 MHz	1	360	420	pF
Output Capacitance	Coss	$V_{GS} = 0 V$		-	80	100	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	42	54	
Total Gate Charge <sup>c</sup>	Qg			1	8.2	12	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = -10 \text{ V}$	$V_{DS} = -20 \text{ V}, I_{D} = -3 \text{ A}$	-	1.1	=.	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	3	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz		3.1	4.1	7	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	7	10	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -20 \text{ V}, \text{ R}_L = 6.7 \Omega$ $I_D \cong -3 \text{ A}, \text{ V}_{GEN} = -10 \text{ V}, \text{ R}_g = 1 \Omega$		=	12	16	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	16	20	ns
Fall Time <sup>c</sup>	t <sub>f</sub>			-	4	8	
Source-Drain Diode Ratings and Chara	acteristics b						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	-10	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = -1.5 A, V <sub>GS</sub> = 0 V		-	-0.8	-1.2	V
		<u> </u>					

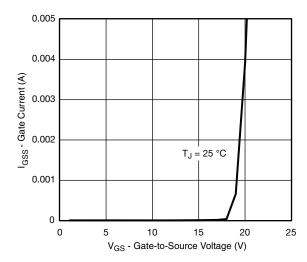
### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

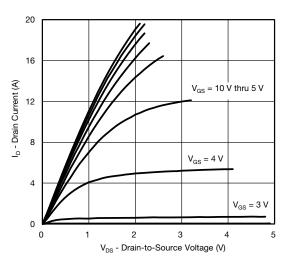
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



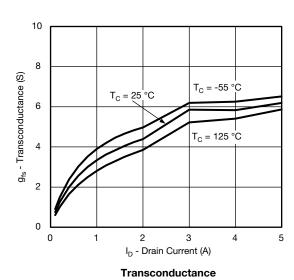
## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

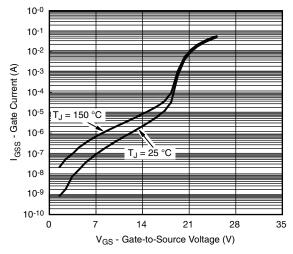


#### Gate Current vs. Gate-Source Voltage

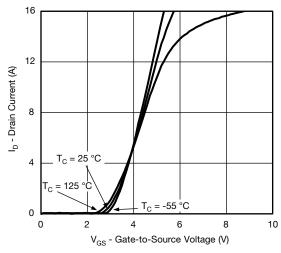


### **Output Characteristics**

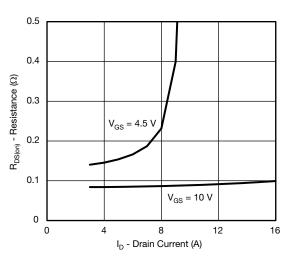




Gate Current vs. Gate-Source Voltage



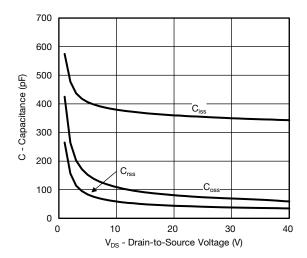
**Transfer Characteristics** 



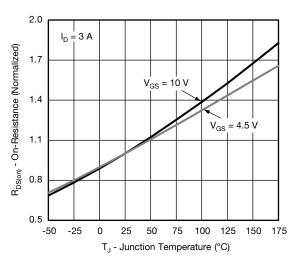
**On-Resistance vs. Drain Current** 



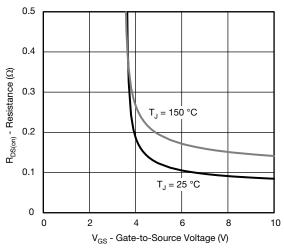
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



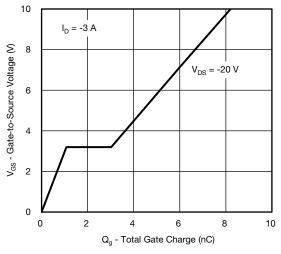
#### Capacitance



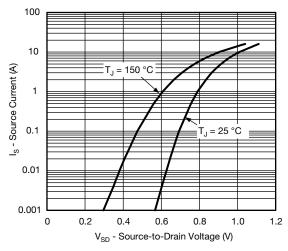
### On-Resistance vs. Junction Temperature



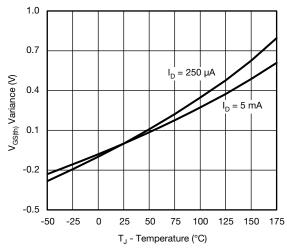
On-Resistance vs. Gate-Source Voltage







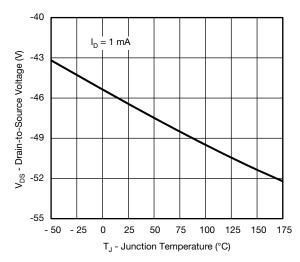
### Source-Drain Diode Forward Voltage



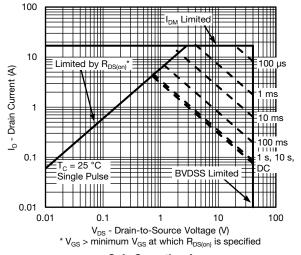
**Threshold Voltage** 



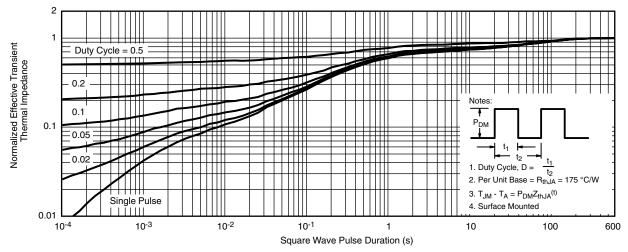
## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



Drain Source Breakdown vs. Junction Temperature



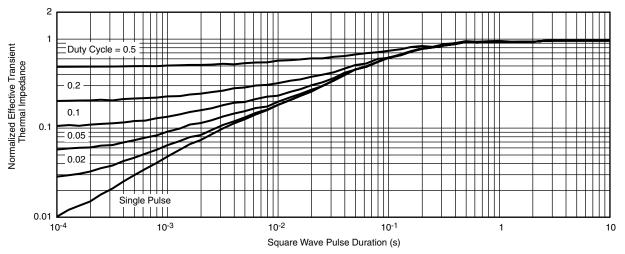
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg263248">www.vishay.com/ppg263248</a>.



# **Ordering Information**

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## **SOT-23**

Ordering codes for the SQ rugged series power MOSFETs in the SOT-23 package:

DATASHEET PART NUMBER	OLD ORDERING CODE a	NEW ORDERING CODE
SQ2301ES	SQ2301ES-T1-GE3	SQ2301ES-T1_GE3
SQ2303ES	SQ2303ES-T1-GE3	SQ2303ES-T1_GE3
SQ2308CES	SQ2308CES-T1-GE3	SQ2308CES-T1_GE3
SQ2309ES	SQ2309ES-T1-GE3	SQ2309ES-T1_GE3
SQ2310ES	SQ2310ES-T1-GE3	SQ2310ES-T1_GE3
SQ2315ES	SQ2315ES-T1-GE3	SQ2315ES-T1_GE3
SQ2318AES	SQ2318AES-T1-GE3	SQ2318AES-T1_GE3
SQ2319ADS	-	SQ2319ADS-T1_GE3
SQ2325ES	SQ2325ES-T1-GE3	SQ2325ES-T1_GE3
SQ2337ES	SQ2337ES-T1-GE3	SQ2337ES-T1_GE3
SQ2348ES	SQ2348ES-T1-GE3	SQ2348ES-T1_GE3
SQ2351ES	SQ2351ES-T1-GE3	SQ2351ES-T1_GE3
SQ2361AEES	SQ2361AEES-T1-GE3	SQ2361AEES-T1_GE3
SQ2361ES		SQ2361ES-T1_GE3
SQ2362ES	-	SQ2362ES-T1_GE3
SQ2389ES	-	SQ2389ES-T1_GE3
SQ2398ES		SQ2398ES-T1_GE3

### Note

a. Old ordering code is obsolete and no longer valid for new orders

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## SOT-23 (TO-236): 3-LEAD







Dim	MILLI	METERS	INCHES		
Dim	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.9	1.90 BSC		8 Ref	
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.6	0.64 Ref 0.025 Ref		5 Ref	
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
FCN: S-03946-Rev K 09-	lul-01	•			

ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479

Document Number: 71196 www.vishay.com 09-Jul-01





# **Mounting LITTLE FOOT® SOT-23 Power MOSFETs**

Wharton McDaniel

Surface-mounted LITTLE FOOT power MOSFETs use integrated circuit and small-signal packages which have been been modified to provide the heat transfer capabilities required by power devices. Leadframe materials and design, molding compounds, and die attach materials have been changed, while the footprint of the packages remains the same.

See Application Note 826, Recommended Minimum Pad Patterns With Outline Drawing Access for Vishay Siliconix MOSFETs, (http://www.vishay.com/doc?72286), for the basis of the pad design for a LITTLE FOOT SOT-23 power MOSFET footprint. In converting this footprint to the pad set for a power device, designers must make two connections: an electrical connection and a thermal connection, to draw heat away from the package.

The electrical connections for the SOT-23 are very simple. Pin 1 is the gate, pin 2 is the source, and pin 3 is the drain. As in the other LITTLE FOOT packages, the drain pin serves the additional function of providing the thermal connection from the package to the PC board. The total cross section of a copper trace connected to the drain may be adequate to carry the current required for the application, but it may be inadequate thermally. Also, heat spreads in a circular fashion from the heat source. In this case the drain pin is the heat source when looking at heat spread on the PC board.

Figure 1 shows the footprint with copper spreading for the SOT-23 package. This pattern shows the starting point for utilizing the board area available for the heat spreading copper. To create this pattern, a plane of copper overlies the drain pin and provides planar copper to draw heat from the drain lead and start the process of spreading the heat so it can be dissipated into the ambient air. This pattern uses all the available area underneath the body for this purpose.



FIGURE 1. Footprint With Copper Spreading

Since surface-mounted packages are small, and reflow soldering is the most common way in which these are affixed to the PC board, "thermal" connections from the planar copper to the pads have not been used. Even if additional planar copper area is used, there should be no problems in the soldering process. The actual solder connections are defined by the solder mask openings. By combining the basic footprint with the copper plane on the drain pins, the solder mask generation occurs automatically.

A final item to keep in mind is the width of the power traces. The absolute minimum power trace width must be determined by the amount of current it has to carry. For thermal reasons, this minimum width should be at least 0.020 inches. The use of wide traces connected to the drain plane provides a low-impedance path for heat to move away from the device.

Document Number: 70739

26-Nov-03



## **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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Revision: 13-Jun-16 1 Document Number: 91000

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